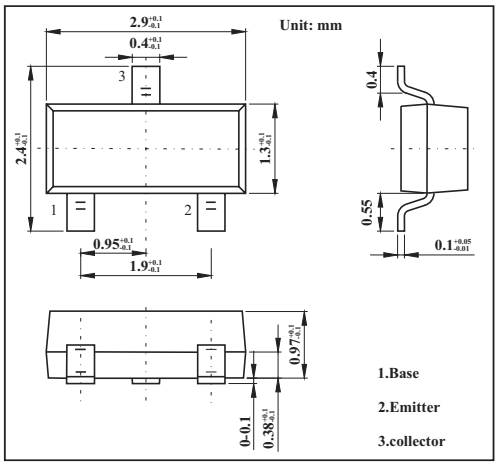
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low $V_{CE(sat)}$.$V_{CE(sat)}$<-0.5V(I_C / I_B = -0.5A /-50mA)
- I_C =-0.8A.
- TRANSISTR (PNP)

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector power dissipation	P_C	0.2	W
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Parameter	Symbol	Test Conditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	VCBO	IC = - 5 0 u A	-40			V
Collector-emitter breakdown voltage	VCEO	IC = -1mA	-32			V
Emitter-base breakdown voltage	VEBO	IE = - 5 0 u A	-5			V
Collector cutoff current	ICBO	VCB = -20V			-0.5	μA
Emitter cutoff current	IEBO	VEB = - 4 V			-0.5	μA
Collector-Emitter Saturation Voltage	VCE(sat)	IC = -0.5A , IB = - 5 0 m A			-0.5	V
DC current transfer ratio	hFE	VCE = - 3 V , I C = -100mA	120		390	
Output Capacitance	Cob	VCB = -10V , IE = 0A , f = 1MHz		12	30	pF
Transition frequency	fT	VCE = - 5 V , I E = 50mA , f = 100MHz		200		MHz